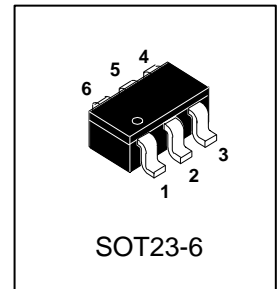


LP3475T1G

30V P-Channel Enhancement-Mode MOSFET

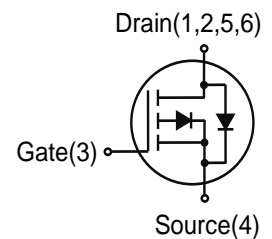
1. FEATURES

- $V_{DS} = -30V$
- $R_{DS(ON)} \leq 65m\Omega @ V_{GS} = -10V$
- $R_{DS(ON)} \leq 90m\Omega @ V_{GS} = -4.5V$
- We declare that the material of product compliance with RoHS requirements and Halogen Free.



2. DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
LP3475T1G	A75	3000/Tape&Reel



3. MAXIMUM RATINGS($T_a = 25^\circ C$)

Parameter	Symbol	Limits	Unit
Drain-Source Voltage	V_{DS}	-30	V
Gate-to-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	ID	$T_a = 25^\circ C$	-4.5
		$T_a = 70^\circ C$	-3.5
Pulsed Drain Current (Note 2)	IDM	-18	A
Avalanche Current	IAS	11	A
Avalanche energy(L=0.1mH)	EAS	6.05	mJ
Power Dissipation (Note 1)	PD	$T_a = 25^\circ C$	1.4
		$T_a = 70^\circ C$	0.9
Junction and Storage Temperature Range	T_j, T_{stg}	-55~+150	$^\circ C$

4. THERMAL CHARACTERISTICS

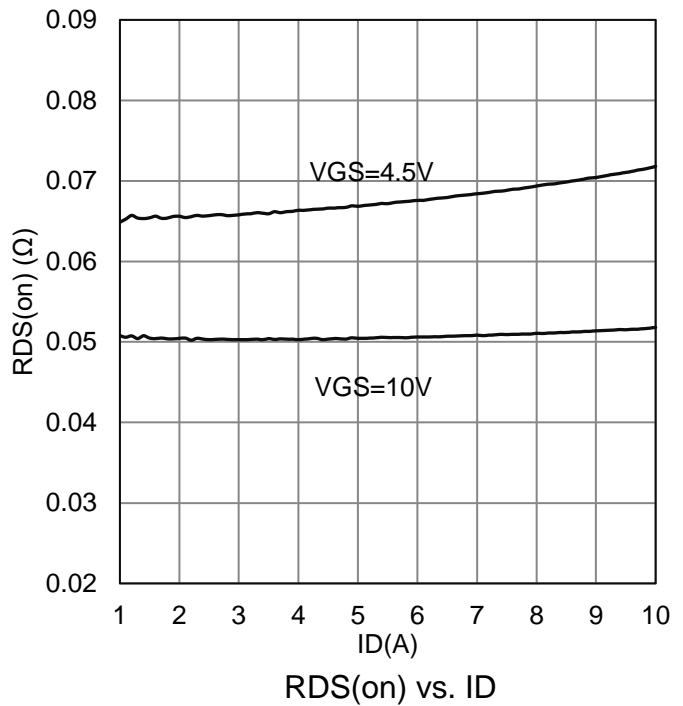
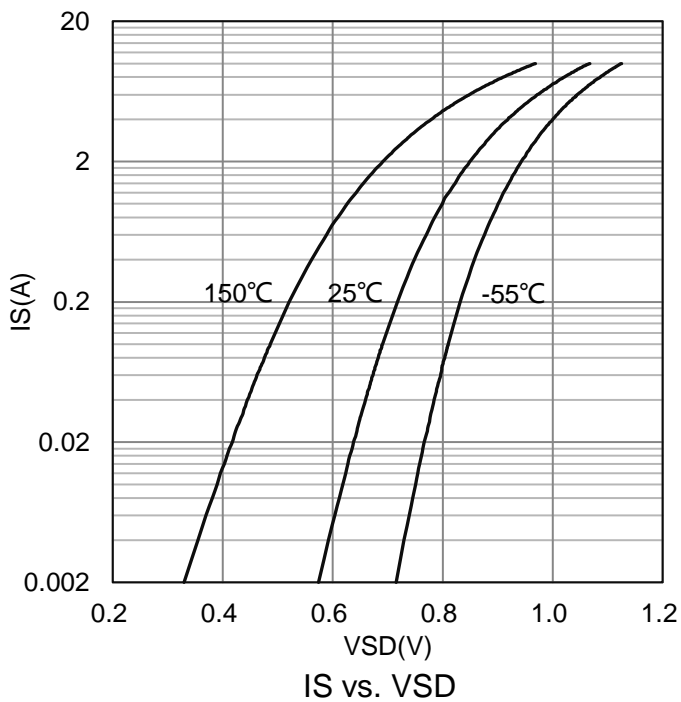
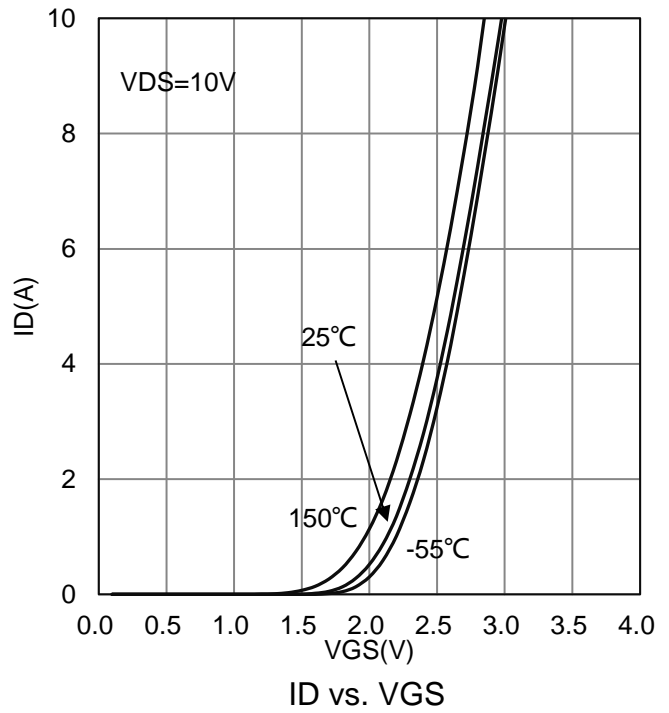
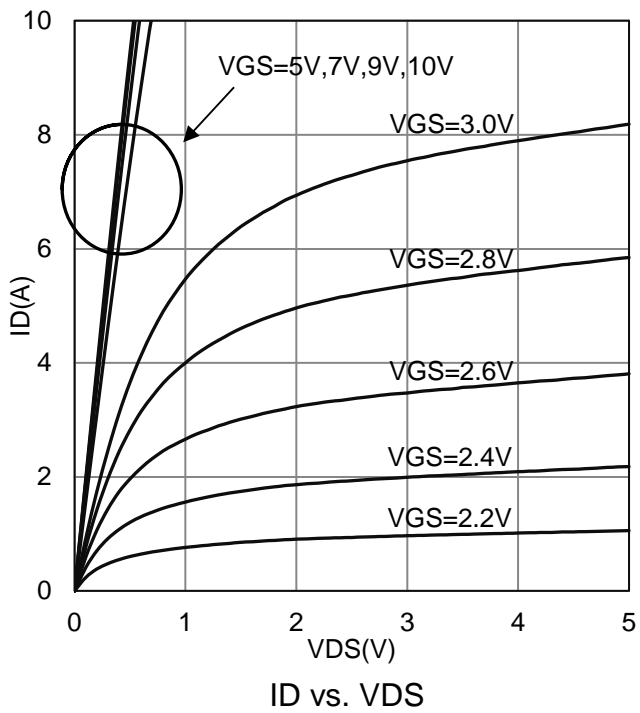
Parameter	Symbol	Limits	Unit
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{\theta JA}$	89	$^\circ C/W$
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	30	$^\circ C/W$

1. Surface mounted on "1.5 x 1.5" FR4 board using 1 sq in pad, 2 oz Cu
2. Pulse width limited by maximum junction temperature

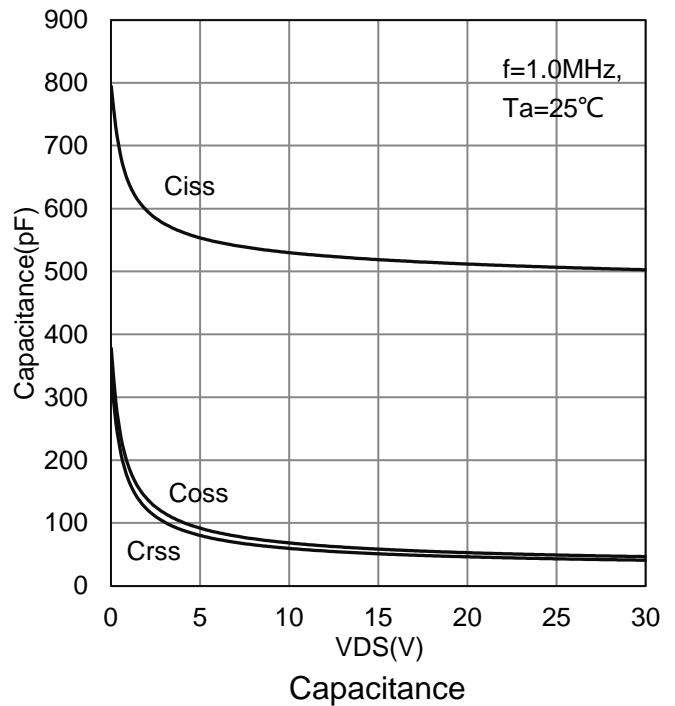
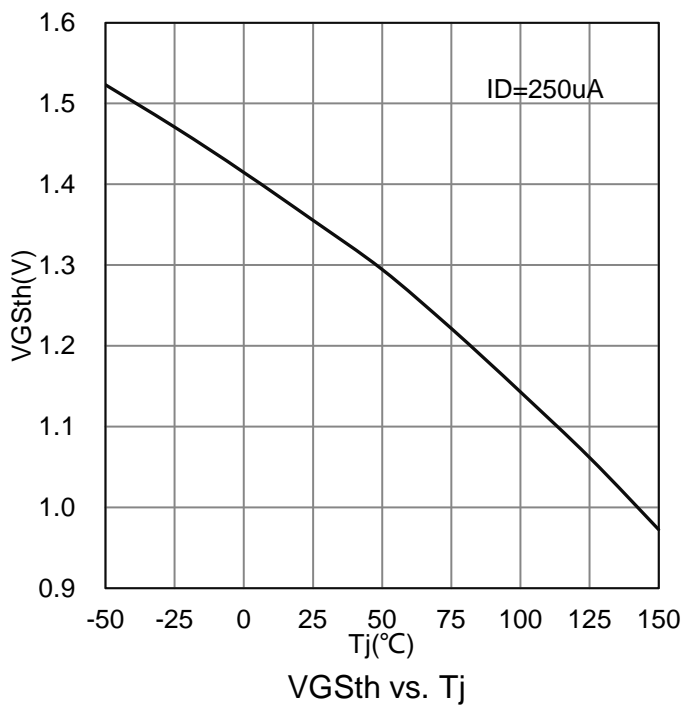
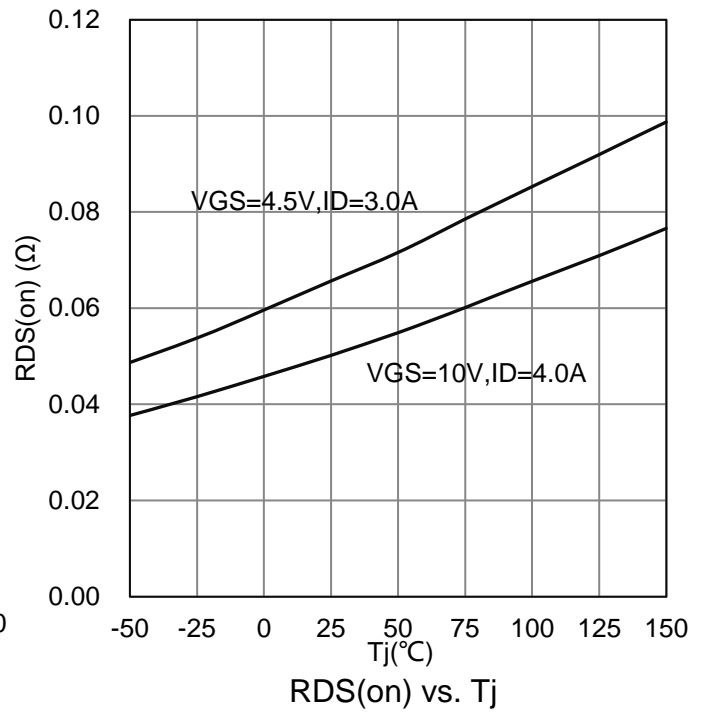
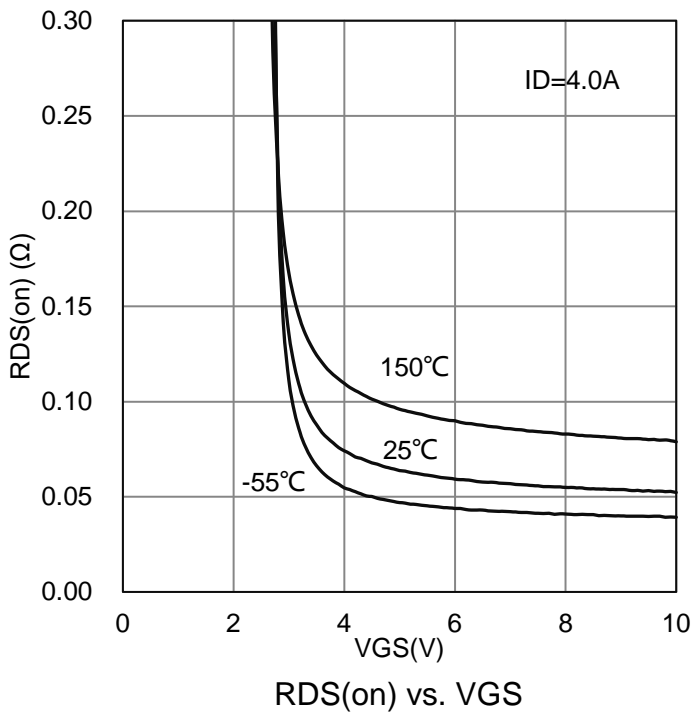
5. ELECTRICAL CHARACTERISTICS (Ta= 25°C)

Characteristic	Symbol	Min.	Typ.	Max.	Unit	
Static						
Drain–Source Breakdown Voltage (VGS = 0, ID = -250μA)	VBRDSS	-30	-	-	V	
Zero Gate Voltage Drain Current (VGS = 0, VDS = -24 V)	IDSS	-	-	-1	μA	
Gate Leakage Current (VDS =0V, VGS =±20V)	IGSS	-	-	±100	nA	
Gate Threshold Voltage (VDS = VGS, ID = -250μA)	VGS(th)	-1	-1.4	-1.6	V	
Static Drain–Source On–State Resistance (VGS =-10V, ID =-4A) (VGS =-4.5V, ID =-3A)	RDS(on)	- -	- -	65 90	mΩ	
Dynamic						
Input Capacitance (VGS = 0 V, f = 1.0MHz, VDS= -15 V)	Ciss	-	534	-	pF	
Output Capacitance (VGS = 0 V, f = 1.0MHz, VDS= -15 V)	Coss	-	60	-		
Reverse Transfer Capacitance (VGS = 0 V, f = 1.0MHz, VDS= -15 V)	Crss	-	52	-		
Gate resistance (VGS =0V, VDS =0V, f=1MHz)	Rg	-	12	-	Ω	
Total Gate Charge	(VDS =-15V, ID =-4A)	Qg(10V)	-	11.4	-	nC
Total Gate Charge		Qg(4.5V)	-	5.6	-	
Gate-Source Charge		Qgs	-	1.3	-	
Gate-Drain Charge		Qgd	-	2.3	-	
Turn-On Delay Time	(VDS = -15V, RL= 3.6 Ω, VGS = -10V, RG = 3Ω)	td(on)	-	3.6	-	ns
Rise Time		tr	-	9.8	-	
Turn-Off Delay Time		td(off)	-	19.2	-	
Fall Time		tf	-	6.7	-	
Forward Voltage (VGS = 0 V, IS = -1A)	VSD	-	-	-1.5	V	

6. ELECTRICAL CHARACTERISTICS CURVES

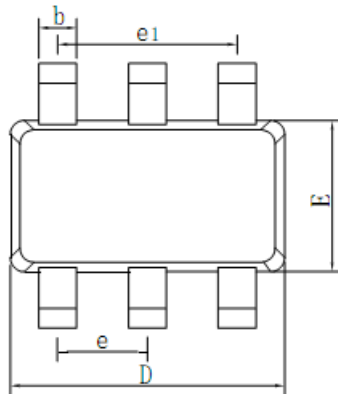
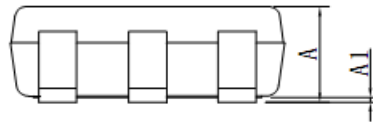
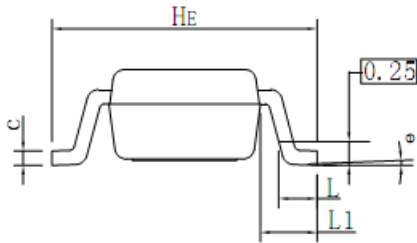


6. ELECTRICAL CHARACTERISTICS CURVES(Con.)



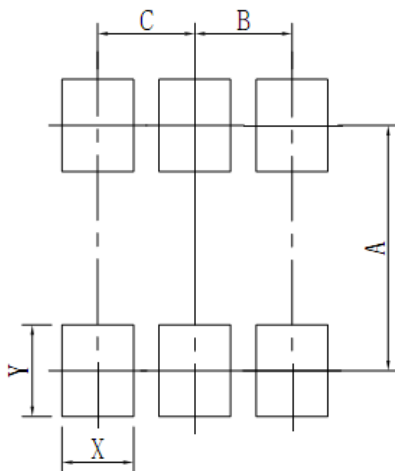
7.OUTLINE AND DIMENSIONS

SOT23-6



SOT23-6			
DIM	MIN	NOR	MAX
A	0.90	1.00	1.10
A1	0.01	0.06	0.10
b	0.25	0.40	0.50
c	0.10	0.17	0.26
D	2.80	2.90	3.10
E	1.30	1.60	1.70
e	0.85	0.95	1.05
e1	1.80	1.90	2.00
L	0.20	0.40	0.60
L1	0.60REF		
HE	2.50	2.80	3.00
θ	0°	-	10°

8.SOLDERING FOOTPRINT



SOT23-6	
DIM	(mm)
X	0.70
Y	0.90
A	2.40
B	0.95
C	0.95

DISCLAIMER

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